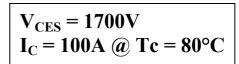
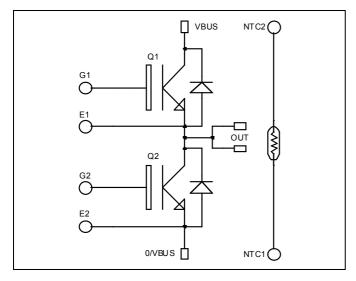


Phase leg Trench + Field Stop IGBT3 Power Module



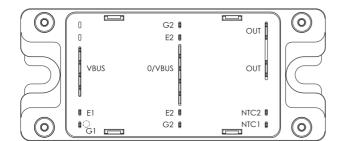


Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

Features

- Trench + Field Stop IGBT3 Technology
 - Low voltage drop
 - Low tail current
 - Switching frequency up to 20 kHz
 - Soft recovery parallel diodes
 - Low diode VF
 - Low leakage current
 - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
 - Symmetrical design
 - Lead frames for power connections
- High level of integration
- Internal thermistor for temperature monitoring



Benefits

- Stable temperature behavior
- Very rugged
- Solderable terminals for easy PCB mounting
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive TC of VCEsat
- Low profile
- RoHS Compliant

Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V_{CES}	Collector - Emitter Breakdown Voltage		1700	V
т	Continuous Collector Current	$T_C = 25$ °C	150	
I_{C}	Continuous Conector Current	$T_C = 80$ °C	100	A
I_{CM}	Pulsed Collector Current	$T_C = 25$ °C	200	
$ m V_{GE}$	Gate – Emitter Voltage		±20	V
P_{D}	Maximum Power Dissipation	$T_C = 25$ °C	560	W
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125$ °C	200A @ 1600V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com



All ratings @ $T_j = 25$ °C unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
I_{CES}	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 1700V$				250	μΑ
V _{CE(sat)}	Collector Emitter Saturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		2.0	2.4	V
V CE(sat)	Conector Emitter Saturation Voltage	$I_{\rm C} = 100 A$	$T_j = 125$ °C		2.4		•
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2mA$		5.0	5.8	6.5	V
I_{GES}	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE}$	= 0V			400	nA

Dynamic Characteristics

	Characteristic	Test Conditions		Min	Тур	Max	Unit
C_{ies}	Input Capacitance	$V_{GE} = 0V$			9		
C_{oes}	Output Capacitance	$V_{CE} = 25V$			0.36		nF
C_{res}	Reverse Transfer Capacitance	f = 1MHz			0.3		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (25°C)			370		
T_{r}	Rise Time	$V_{GE} = 15V$			40		ns
T _{d(off)}	Turn-off Delay Time	$V_{Bus} = 900V$ $I_{C} = 100A$			650		
T_{f}	Fall Time	$R_G = 4.7 \Omega$			180		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching (125°C)		400		
T_{r}	Rise Time	$V_{GE} = 15V$			50		
$T_{d(off)}$	Turn-off Delay Time	$V_{Bus} = 900V$ $I_C = 100A$			800		ns
T_{f}	Fall Time	$R_G = 4.7 \Omega$			300		
Eon	Turn-on Switching Energy	$V_{GE} = 15V$ $V_{Bus} = 900V$ $T_{j} = 15V$	= 125°C		32	·	m I
$\mathrm{E}_{\mathrm{off}}$	Turn-off Switching Energy	$\begin{bmatrix} I_C = 100A \\ R_G = 4.7 \Omega \end{bmatrix} T_j =$	= 125°C		31		mJ

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions		Min	Typ	Max	Unit
V_{RRM}	Maximum Peak Repetitive Reverse Voltage			1700			V
I_{RM}	Maximum Reverse Leakage Current	$V_{R}=1700V$	$T_j = 25^{\circ}C$			250	μΑ
1KM	Waxiiiaiii reveise Beakage Caireit	VR 1700 V	$T_j = 125$ °C			500	μπ
I_{F}	DC Forward Current		$Tc = 80^{\circ}C$		100		A
V_{F}	Diode Forward Voltage	$I_{\rm F} = 100A$	$T_j = 25$ °C		1.8	2.2	V
▼ F	Blode Forward Voluge	1 _F 10071	$T_{i} = 125^{\circ}C$		1.9		_ *
t _{rr}	Reverse Recovery Time		$T_j = 25^{\circ}C$		385		ns
·rr	reverse recovery Time	1 100 4	$T_j = 125$ °C		490		115
Q _{rr}	Reverse Recovery Charge	$I_F = 100A$ $V_R = 900V$	$T_j = 25^{\circ}C$		25		μС
Qrr	Reverse Recovery Charge	$di/dt = 1000A/\mu s$	$T_{j} = 125^{\circ}C$		42		μС
E_{r}	D		$T_j = 25^{\circ}C$		11		mJ
\mathbf{L}_{r}	Reverse Recovery Energy		$T_j = 125$ °C		21		1113



 $Temperature\ sensor\ NTC\ (see\ application\ note\ APT0406\ on\ www.microsemi.com\ for\ more\ information).$

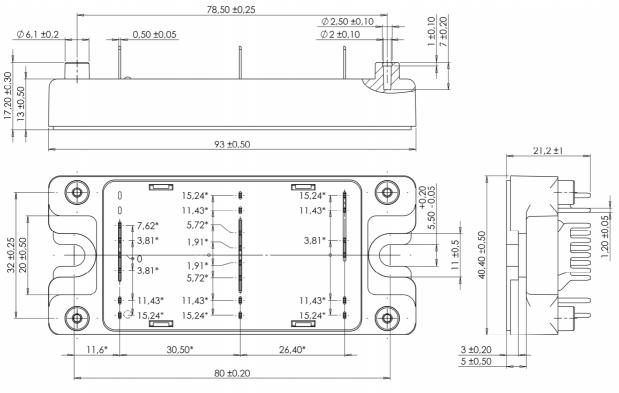
Symbol	Characteristic	Min	Тур	Max	Unit	
R ₂₅	Resistance @ 25°C		50		kΩ	
${ m B}_{25/85}$	$T_{25} = 298.15 \text{ K}$		3952		K	

$$R_T = \frac{R_{25}}{\exp \left[B_{25/85} \left(\frac{1}{T_{25}} - \frac{1}{T} \right) \right]}$$
 T: Thermistor temperature R_T: Thermistor value at T

Thermal and package characteristics

Symbol	Characteristic			Min	Typ	Max	Unit
R_{thJC}	Junction to Case Thermal Resistance		IGBT			0.22	°C/W
KthJC			Diode			0.39	
V_{ISOL}	RMS Isolation Voltage, any terminal to case t =	1 min, 50/60Hz		4000			V
T_{J}	Operating junction temperature range Storage Temperature Range			-40		150	
T_{STG}			-40		125	°C	
$T_{\rm C}$	Operating Case Temperature			-40		100	
Torque	Mounting torque	To Heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

SP4 Package outline (dimensions in mm)

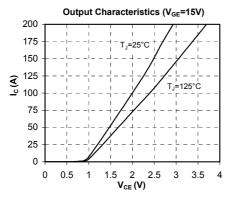


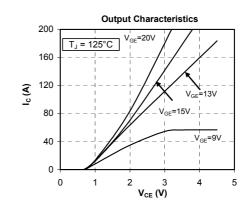
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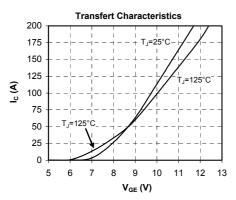
See application note APT0501 - Mounting Instructions for SP4 Power Modules on www.microsemi.com

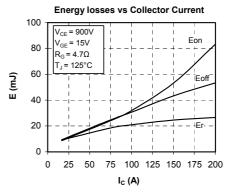


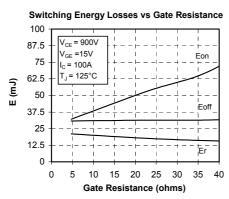
Typical Performance Curve

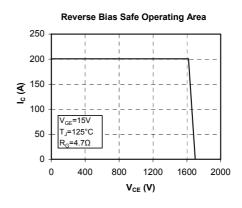


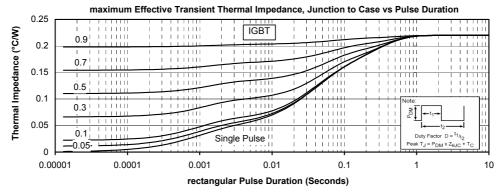




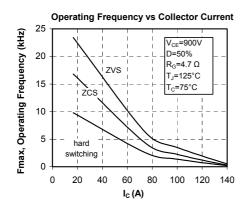


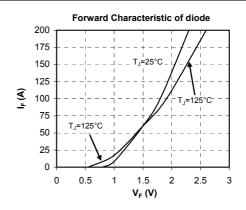


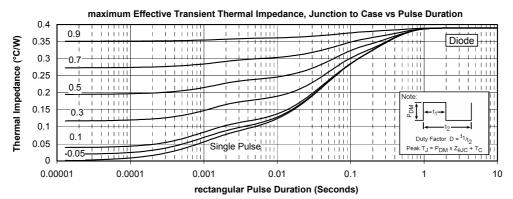














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